

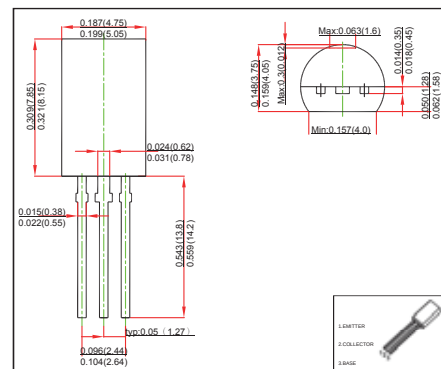
TO-92L Plastic-Encapsulate Transistors

FEATURES

- Power Amplifier Applications
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-92L molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current –Continuous	I_C	-2	A
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55-150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -2V, I_C = -0.5A$	70		240	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -1.5A$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -50mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1A, I_B = -50mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -2V, I_C = -500mA$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		40		pF
Turn-on time	t_{on}	$V_{CC} = -30V, I_{B1} = -I_{B2} = -0.05A, I_C = -1A$		0.1		μs
Storage time	t_s			1		μs
Fall time	t_f			0.1		μs